RF2374 3V LOW NOISE AMPLIFIER

Package Style: QFN, 8-Pin, 2.2mmx2.2mmx0.55mm



Features

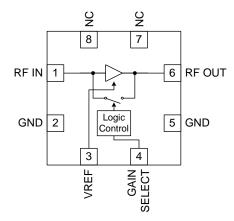
RFMD

rfmd.com

- Low Noise and High Intercept Point
- Adjustable Bias Current
- Power Down Control
- Low Insertion Loss Bypass Feature
- 1.8V to 4V Operation (See Note: Page 2)
- 800 MHz to 3.8GHz Operation
- ESD Class 1B

Applications

- WiFi LNA with Bypass Feature
- CDMA PCS LNA with Bypass Feature
- GPS LNA with Bypass Feature
- General Purpose Amplification
- WiMAX LNA with Bypass Function
- CDMA 800 LNA
- CMMB LNA
- LTE Bands LNA



Functional Block Diagram

Product Description

The RF2374 is a switchable low noise amplifier with a high dynamic range designed for digital cellular and WiFi applications. The device functions as an outstanding front end low noise amplifier with I_{CC} as low as 3 mA. The bias current may be set externally. The IC is featured in a 2.2 mmx2.2 mmx0.6 mm module-compatible plastic package.

Optimum Technolog	y Matching® App	lied
SiGe BiCMOS	GaAs pHFMT	GaN HEMT

SiGe BiCMOS	🗌 GaAs pHEMT
Si BiCMOS	Si CMOS
SiGe HBT	🗌 Si BJT
	Si BiCMOS

RF MICRO DEVICES®, RFMD®, Optimum Technology Matching®, Enabling Wireless Connectivity^M, PowerStar®, POLARIS^M TOTAL RADIO^M and UttimateBlue^M are trademarks of RFMD, LLC. BLUETOOTH is a trade mark owned by Bluetooth SIG, Inc., U.S.A. and licensed for use by RFMD. All other trade names, trademarks and registered trademarks are the property of their respective owners. ©2006, RF Micro Devices, Inc.

7628 Thorndike Road, Greensboro, NC 27409-9421 · For sales or technical support, contact RFMD at (+1) 336-678-5570 or sales-support@rfmd.com.

□ BIFET HBT □ LDMOS

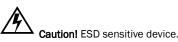




Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.5 to +6.0	V _{DC}
Input RF Level at F<2.3GHz	+5 (see note)	dBm
Input RF Level at F>2.3GHz	+10 (see note)	dBm
Current Drain, I _{CC}	32	mA
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C

NOTE: Exceeding any one or a combination of the above maximum rating limits may cause permanent damage. Input RF transients to +15dBm will not harm the device. For sustained operation at inputs \geq +5 dBm, a small dropping resistor is recommended in series with the $V_{\mbox{CC}}$ in order to limit the current due to self-biasing to <32 mA. Furthermore, while the LNA is in Bypass Mode, and for sustained operation at the input, +10dBm is the maximum recommended power level for Frequencies above 2300MHz. +5dBm is the maximum recommended power level for Frequencies <2300 MHz.



Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical perfor-mance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

The information in this publication is believed to be accurate and reliable. However, no responsibility is assumed by RF Micro Devices, Inc. ("RFMD") for its use, nor for any infringement of patents, or other rights of third parties, resulting from its use. No license is granted by implication or otherwise under any patent or patent rights of RFMD. RFMD reserves the right to change component circuitry, recommended application circuitry and specifications at any time without prior notice.

Dowowedaw	Specification		11	Ocus diki cu		
Parameter	Min.	Тур.	Max.	Unit	Condition	
Operating Range					T _{AMB} =+25°C, V _{CC} =3.0V	
Frequency Range	50		4000	MHz		
WiBRO/WiFi/WiMAX Low Noise Amplifier						
Frequency	2300		2700	MHz		
HIGH GAIN MODE					Gain Select<0.8V, V _{REF} =3V, T=+25°C	
Gain	13.5	14.5		dB		
Noise Figure		1.3	1.5	dB		
Input IP3	+7	+9		dBm	IIP3 will improve if I_{CC} is raised above 7 mA.	
IP1dB	0			dBm		
Current Drain		7		mA		
BYPASS MODE (Low Gain)					Gain Select≥1.6V	
Gain	-4.0	-3.0	-2.0	dB	Note: Bypass mode insertion loss will degrade gradually as $V_{\mbox{CC}}$ goes below 2.7V.	
Input IP3	+20	+21		dBm		
Current Drain		2.8	3.0	mA	Current drain includes I _{CC} +I _{REF}	
GPS Low Noise Amplifier						
Frequency		1575		MHz		
Gain		17.5		dB	I _{CC} =6.5mA, I _{CC} +I _{REF} =7.5mA	
Noise Figure		1.2		dB		
Input IP3		+7.0		dBm		
WiMAX Low Noise Amplifier						
Frequency	3100	3500	3800	MHz	I _{CC} =7mA	
Gain		11.0		dB		
Noise Figure		1.6		dB		
Input IP3		+10.0		dBm	IIP3 will improve if I _{CC} is raised above 7 mA.	
BYPASS MODE (Low Gain)						
Gain		-3.0	-2.5	dB		
Input IP3	20.5	22.0		dBm		





Parameter	Specification			Unit	Condition
	Min.	Тур.	Max.	Unit	Condition
CDMA Low Noise Amplifier					
HIGH GAIN MODE					
Frequency	869		894	MHz	
Gain		19		dB	
Noise Figure		1.0		dB	
Input IP3		+2.0		dBm	IIP3 will improve if I _{CC} is raised above 7 mA.
Current Drain		7		mA	
Low Band LNA					
HIGH GAIN MODE					
Frequency	50		950	MHz	
Gain		20		dB	88MHz
Gain		19		dB	870MHz
Noise Figure		2.5		dB	88MHz
Noise Figure		1.5		dB	870 MHz
Input IP3		+2.0		dBm	IIP3 will improve if I _{CC} is raised above 7 mA.
PCS and LTE Band LNA					V _{CC} =2.2V, 25°C
Frequency	1750		2050	MHz	
HIGH GAIN MODE					Gain Select<0.8V
Gain	15	16		dB	
Noise Figure		1.1	1.3	dB	
Input IP3	8	9	10	dBm	IIP3 will improve if I _{CC} is raised above 7 mA
Current Drain		7		mA	
BYPASS MODE (Low Gain)					Gain Select>1.6V
Gain	-3	-2		dB	
Input IP3	17	18		dBm	
Noise Figure		2.7	3.5	dB	
LTE Low Band LNA					V _{CC} =2.2V, 25°C
Frequency	704		950	MHz	
HIGH GAIN MODE					Gain Select<0.8V
Gain	17	18		dB	
Noise Figure		1.4	1.6	dB	
Input IP3	-3	0		dBm	IIP3 will improve if I _{CC} is raised above 7 mA
Current Drain		7		mA	
BYPASS MODE (Low Gain)					
Gain	-5	-4		dB	
Input IP3	14	15		dBm	
Noise Figure		5	6.6	dB	



RFMD	• ›))))®
rfmd.com	

Parameter		Specification		Unit	Condition	
Farameter	Min.	Тур.	Max.	Unit	Condition	
Power Supply						
Voltage (V _{CC})		3		V		
Gain Select Low Level (High Gain Mode)			0.8	V	High Gain mode. Gain Select<0.8V, V _{REF} =3V (typical)	
Gain Select High Level (Bypass Mode)	1.6			V	Low Gain mode. Gain Select≥1.6V, V _{REF} : see bias note 2	
Gain Select On/Off Time			<150	nSec	(C1 values range from 3 to 10 pF), Temp=-40°C to +85°C, and over process	
Power Down	0		5	μΑ	Gain Select<0.8V, V _{REF} =0V, V _{CC} =3.0V	

Bias note: Due to the presence of ESD protection circuitry on the RF2374, the maximum allowable collector bias voltage (pin 6) is 4.0V. Higher supply voltages such as 5V are permissible if a series resistor is used to drop V_{CC} to ≤4.0V for a given I_{CC}. Bias note 2: In bypass mode, V_{REF} is essentially a "don't care" condition. Pulling V_{REF} low when in bypass mode does conserve the small 1mA

to 2mA supplied by V_{REF} .

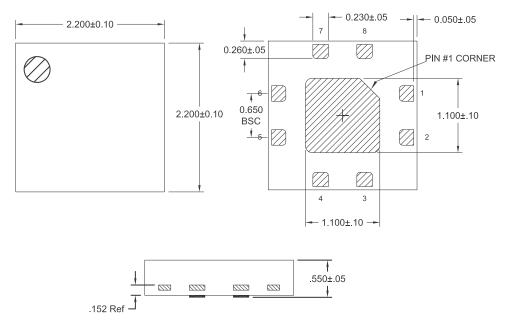


rfmd.com

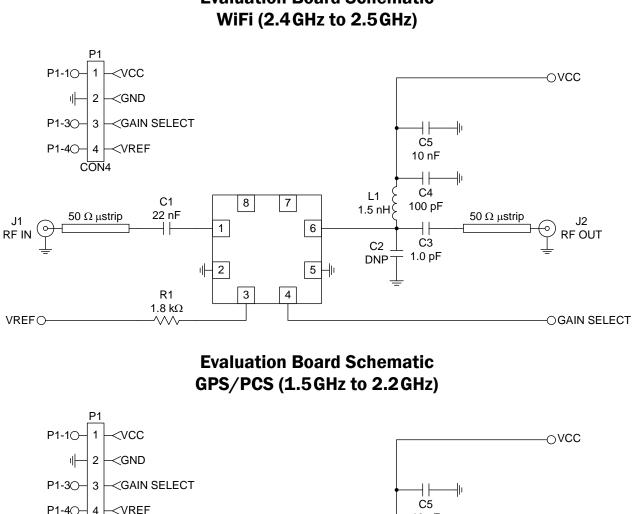


Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This part is designed such that 50Ω is the optimal source impedance for best noise figure. Best noise figure is achieved with only a series capacitor on the input.	To Bias Circuit RF IN O
2	GND1	Ground connection. For best performance, keep traces physically short and connect immediately to ground plane.	
3	VREF	For low noise amplifier applications, this pin is used to control the bias current. An external resistor can be used to set the bias current for any V_{BIAS} voltage. This device will have good gain and noise figure with I_{CC} as low as 3mA.	VREF
4	GAIN SELECT	This pin selects high gain and bypass modes. Gain Select≤0.8V, high gain. Gain Select≥1.6V, low gain.	
5	GND2	See GND1.	
6	RF OUT	Amplifier output pin. This pin is an open-collector output. It must be biased to $\rm V_{\rm CC}$ through a choke or matching inductor.	
7	NC	Not connected.	
8	NC	Not connected.	
Pkg Gnd	GND	This pad should be connected to the ground plane by vias directly under the device.	

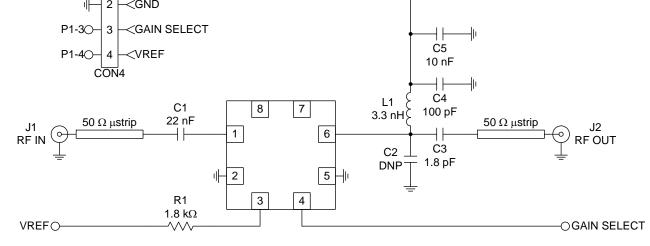
Package Drawing







Evaluation Board Schematic

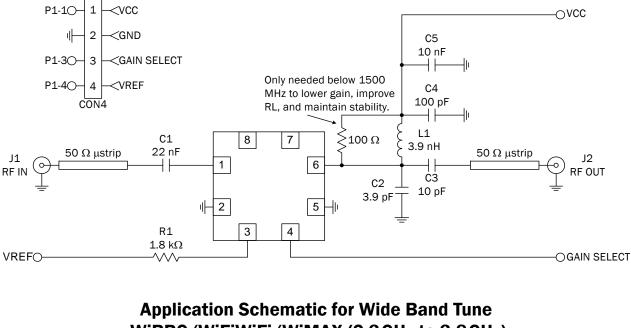


VREF O-

 $\sim \sim \sim$

OGAIN SELECT

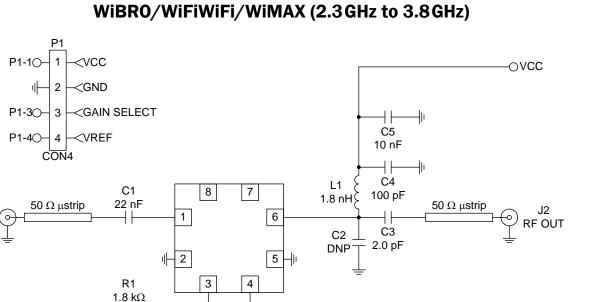
Application Schematic - 869 MHz to 894 MHz Tune



P1 <vcc 1 P1-1C -OVCC ᆘ 2 <GND P1-30-3 <GAIN SELECT -||+ C5 P1-40-<VREF 4 10 nF CON4 ┥┝ C4 L1 C1 8 7 100 pF 1.8 nH⋩ 50 Ω µstrip 22 nF 50 Ω µstrip J1 J2 1 6 RF IN C3 C2



Ρ1







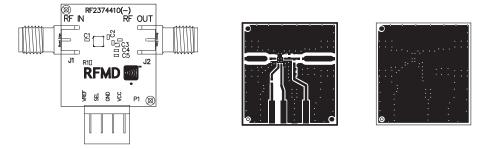


1 2 바 GAIN SELECT O 3 VREF O-4 -O VCC CON4 ++-11-C5 C6 10 nF R2 1000 pF $1.2 \ \text{K}\Omega$ +++ + \sim C4 100 pF L1 100 nH 8 7 C1 СЗ 22 nF 100 pF J2 1 6 41 ++RFOUT C2 СЗ DNP 5 ᆘ 2 DNP 3 4 R1 1.8 KΩ VREF O- $\sim \sim$ - GAIN SELECT

Application Schematic for Low Band Tune

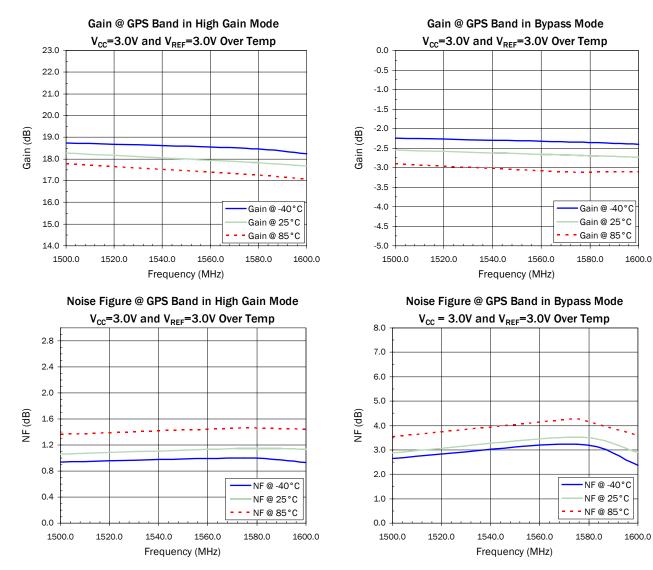
Evaluation Board Layout Board Size 0.835" x 0.900"

Board Thickness 0.032", Board Material FR-4





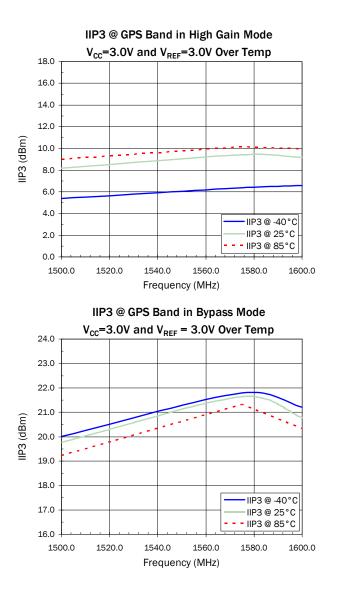


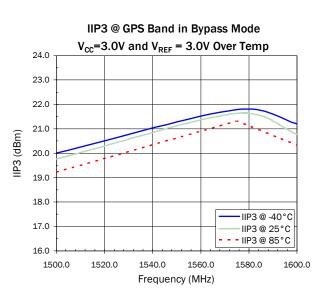


GPS Band Data





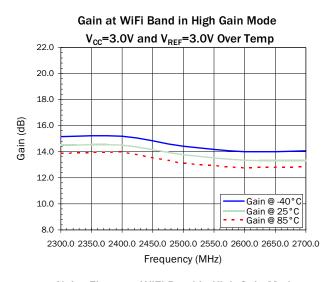


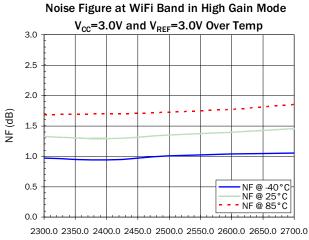


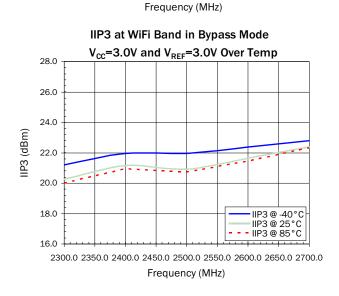


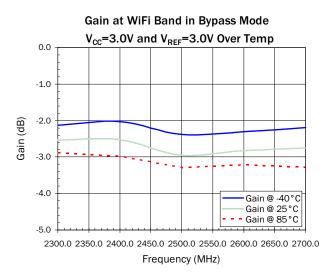


WiBRO/WiFi/WiMAX Data

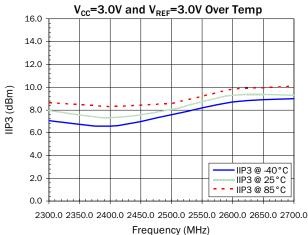


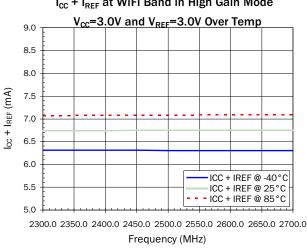






IIP3 at WiFi Band in High Gain Mode



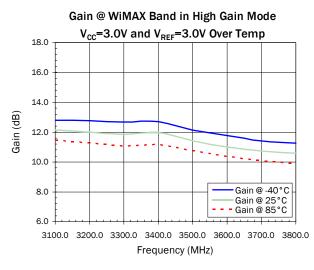


I_{CC} + I_{REF} at WiFi Band in High Gain Mode

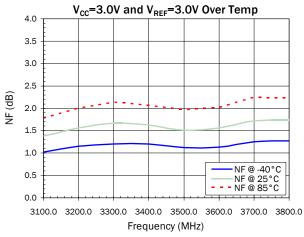


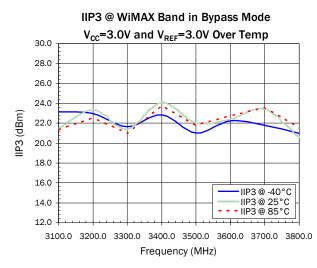


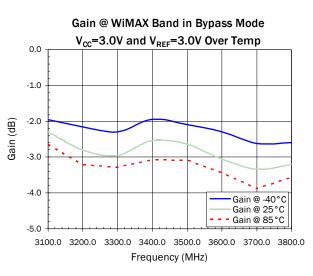
WiMAX Data

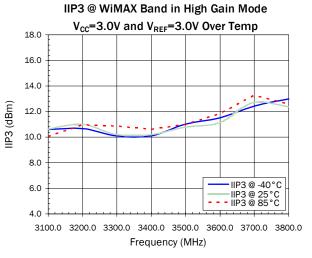


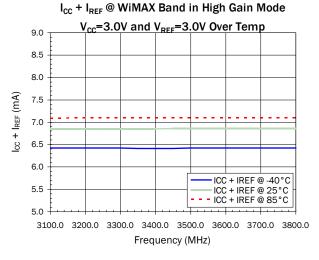




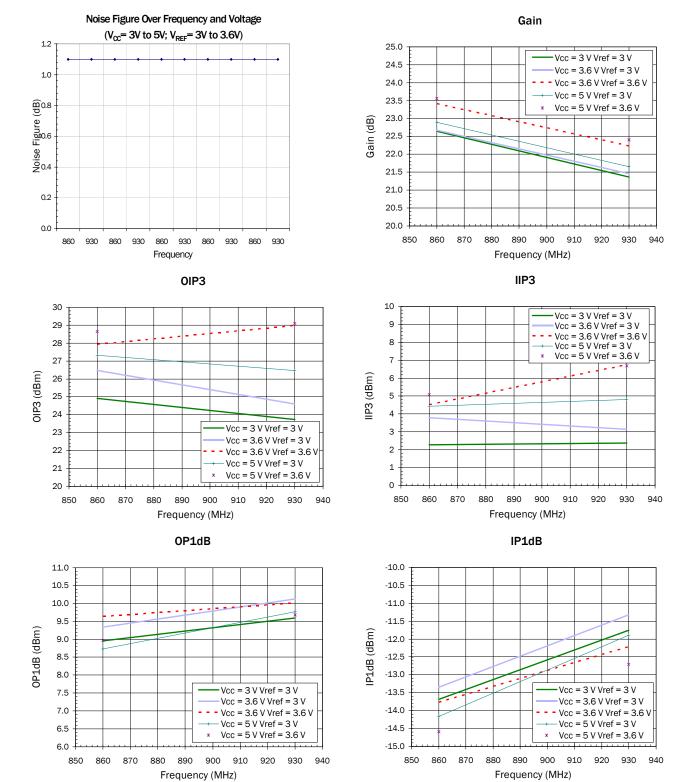








CDMA Data



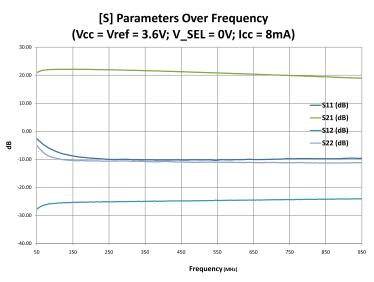


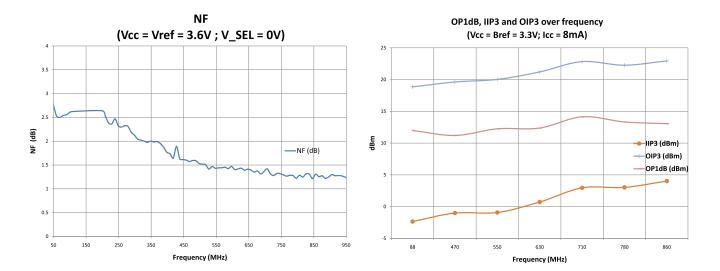






Low Band Tune Data







Ordering Information

Ordering Code	Description
RF2374	Standard 25 piece bag
RF2374SR	Standard 100 piece reel
RF2374TR7	Standard 2500 piece reel
RF2374PCK-410	Fully assembled evaluation board tuned for 2.4GHz to 2.5GHz with standard tune
RF2374PCK-411	Fully assembled evaluation board tuned for 1.5GHz to 2.2GHz with standard tune